

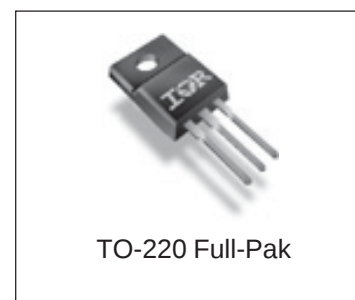
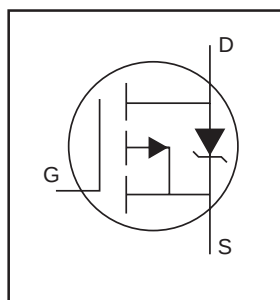
## IRLIB9343PbF

## Features

- Advanced Process Technology
- Key Parameters Optimized for Class-D Audio Amplifier Applications
- Low  $R_{DS(ON)}$  for Improved Efficiency
- Low  $Q_g$  and  $Q_{sw}$  for Better THD and Improved Efficiency
- Low  $Q_{rr}$  for Better THD and Lower EMI
- 175°C Operating Junction Temperature for Ruggedness
- Repetitive Avalanche Capability for Robustness and Reliability
- Lead-Free

## Key Parameters

|                                      |     |    |
|--------------------------------------|-----|----|
| $V_{DS}$                             | -55 | V  |
| $R_{DS(ON)}$ typ. @ $V_{GS} = -10V$  | 93  | mΩ |
| $R_{DS(ON)}$ typ. @ $V_{GS} = -4.5V$ | 150 | mΩ |
| $Q_g$ typ.                           | 31  | nC |
| $T_J$ max                            | 175 | °C |



## Description

This Digital Audio HEXFET® is specifically designed for Class-D audio amplifier applications. This MosFET utilizes the latest processing techniques to achieve low on-resistance per silicon area. Furthermore, Gate charge, body-diode reverse recovery and internal Gate resistance are optimized to improve key Class-D audio amplifier performance factors such as efficiency, THD and EMI. Additional features of this MosFET are 175°C operating junction temperature and repetitive avalanche capability. These features combine to make this MosFET a highly efficient, robust and reliable device for Class-D audio amplifier applications.

## Absolute Maximum Ratings

|                             | Parameter                                        | Max.         | Units        |
|-----------------------------|--------------------------------------------------|--------------|--------------|
| $V_{DS}$                    | Drain-to-Source Voltage                          | -55          | V            |
| $V_{GS}$                    | Gate-to-Source Voltage                           | ±20          |              |
| $I_D$ @ $T_C = 25^\circ C$  | Continuous Drain Current, $V_{GS}$ @ -10V        | -14          | A            |
| $I_D$ @ $T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS}$ @ -10V        | -10          |              |
| $I_{DM}$                    | Pulsed Drain Current ①                           | -60          |              |
| $P_D$ @ $T_C = 25^\circ C$  | Power Dissipation                                | 33           | W            |
| $P_D$ @ $T_C = 100^\circ C$ | Power Dissipation                                | 20           |              |
|                             | Linear Derating Factor                           | 0.26         | W/°C         |
| $T_J$                       | Operating Junction and Storage Temperature Range | -40 to + 175 | °C           |
|                             | Mounting Torque, 6-32 or M3 screw                | 10 (1.1)     | lbf•in (N•m) |

## Thermal Resistance

|                 | Parameter             | Typ. | Max. | Units |
|-----------------|-----------------------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case ④    | —    | 3.84 | °C/W  |
| $R_{\theta JA}$ | Junction-to-Ambient ④ | —    | 65   |       |

Notes ① through ⑤ are on page 7

**Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

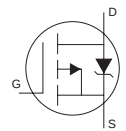
|                                | Parameter                            | Min. | Typ. | Max. | Units                | Conditions                                            |
|--------------------------------|--------------------------------------|------|------|------|----------------------|-------------------------------------------------------|
| $BV_{DSS}$                     | Drain-to-Source Breakdown Voltage    | -55  | —    | —    | V                    | $V_{GS} = 0V, I_D = -250\mu A$                        |
| $\Delta BV_{DSS}/\Delta T_J$   | Breakdown Voltage Temp. Coefficient  | —    | -52  | —    | mV/ $^\circ\text{C}$ | Reference to $25^\circ\text{C}$ , $I_D = -1\text{mA}$ |
| $R_{DS(on)}$                   | Static Drain-to-Source On-Resistance | —    | 93   | 105  | $m\Omega$            | $V_{GS} = -10V, I_D = -3.4A$ ③                        |
|                                |                                      | —    | 150  | 170  |                      | $V_{GS} = -4.5V, I_D = -2.7A$ ③                       |
| $V_{GS(th)}$                   | Gate Threshold Voltage               | -1.0 | —    | —    | V                    | $V_{DS} = V_{GS}, I_D = -250\mu A$                    |
| $\Delta V_{GS(th)}/\Delta T_J$ | Gate Threshold Voltage Coefficient   | —    | -3.7 | —    | mV/ $^\circ\text{C}$ |                                                       |
| $I_{DSS}$                      | Drain-to-Source Leakage Current      | —    | —    | -2.0 | $\mu A$              | $V_{DS} = -55V, V_{GS} = 0V$                          |
|                                |                                      | —    | —    | -25  |                      | $V_{DS} = -55V, V_{GS} = 0V, T_J = 125^\circ\text{C}$ |
| $I_{GSS}$                      | Gate-to-Source Forward Leakage       | —    | —    | -100 | nA                   | $V_{GS} = -20V$                                       |
|                                | Gate-to-Source Reverse Leakage       | —    | —    | 100  |                      | $V_{GS} = 20V$                                        |
| $g_{fs}$                       | Forward Transconductance             | 5.3  | —    | —    | S                    | $V_{DS} = -25V, I_D = -14A$                           |
| $Q_g$                          | Total Gate Charge                    | —    | 31   | 47   |                      | $V_{DS} = -44V$                                       |
| $Q_{gs}$                       | Pre-Vth Gate-to-Source Charge        | —    | 7.1  | —    |                      | $V_{GS} = -10V$                                       |
| $Q_{gd}$                       | Gate-to-Drain Charge                 | —    | 8.5  | —    |                      | $I_D = -14A$                                          |
| $Q_{godr}$                     | Gate Charge Overdrive                | —    | 15   | —    |                      | See Fig. 6 and 19                                     |
| $t_{d(on)}$                    | Turn-On Delay Time                   | —    | 9.5  | —    | ns                   | $V_{DD} = -28V, V_{GS} = -10V$ ③                      |
| $t_r$                          | Rise Time                            | —    | 24   | —    |                      | $I_D = -14A$                                          |
| $t_{d(off)}$                   | Turn-Off Delay Time                  | —    | 21   | —    |                      | $R_G = 2.5\Omega$                                     |
| $t_f$                          | Fall Time                            | —    | 9.5  | —    |                      |                                                       |
| $C_{iss}$                      | Input Capacitance                    | —    | 660  | —    | pF                   | $V_{GS} = 0V$                                         |
| $C_{oss}$                      | Output Capacitance                   | —    | 160  | —    |                      | $V_{DS} = -50V$                                       |
| $C_{rss}$                      | Reverse Transfer Capacitance         | —    | 72   | —    |                      | $f = 1.0\text{MHz}$ , See Fig.5                       |
| $C_{oss}$                      | Effective Output Capacitance         | —    | 280  | —    |                      | $V_{GS} = 0V, V_{DS} = 0V$ to $-44V$                  |
| $L_D$                          | Internal Drain Inductance            | —    | 4.5  | —    | nH                   | Between lead,<br>6mm (0.25in.)                        |
| $L_S$                          | Internal Source Inductance           | —    | 7.5  | —    |                      | from package<br>and center of die contact             |

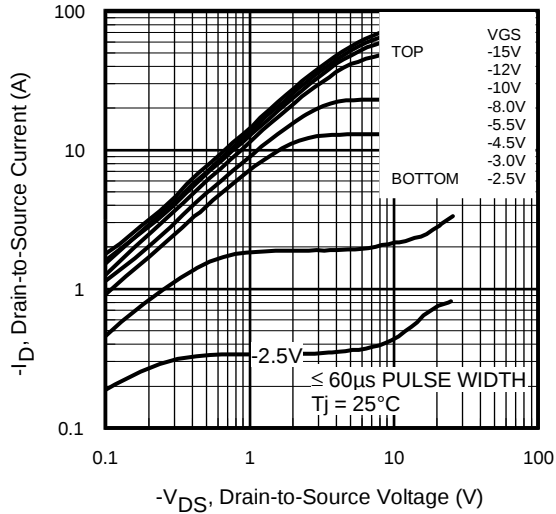
**Avalanche Characteristics**

|          | Parameter                      | Typ.                      | Max. | Units |
|----------|--------------------------------|---------------------------|------|-------|
| $E_{AS}$ | Single Pulse Avalanche Energy② | —                         | 190  | mJ    |
| $I_{AR}$ | Avalanche Current ⑤            | See Fig. 14, 15, 17a, 17b |      | A     |
| $E_{AR}$ | Repetitive Avalanche Energy ⑤  |                           |      | mJ    |

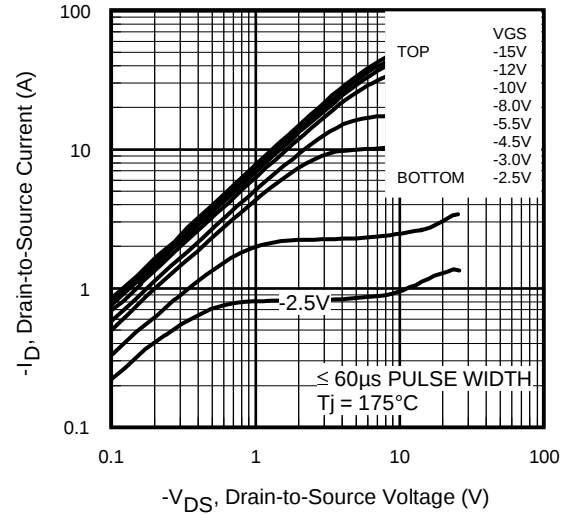
**Diode Characteristics**

|                                | Parameter                                 | Min. | Typ. | Max. | Units | Conditions                                                              |
|--------------------------------|-------------------------------------------|------|------|------|-------|-------------------------------------------------------------------------|
| $I_S @ T_C = 25^\circ\text{C}$ | Continuous Source Current<br>(Body Diode) | —    | —    | -14  | A     | MOSFET symbol<br>showing the<br>integral reverse<br>p-n junction diode. |
| $I_{SM}$                       | Pulsed Source Current<br>(Body Diode) ①   | —    | —    | -60  |       |                                                                         |
| $V_{SD}$                       | Diode Forward Voltage                     | —    | —    | -1.2 | V     | $T_J = 25^\circ\text{C}, I_S = -14A, V_{GS} = 0V$ ③                     |
| $t_{rr}$                       | Reverse Recovery Time                     | —    | 57   | 86   | ns    | $T_J = 25^\circ\text{C}, I_F = -14A$                                    |
| $Q_{rr}$                       | Reverse Recovery Charge                   | —    | 120  | 180  | nC    | $di/dt = 100A/\mu s$ ③                                                  |

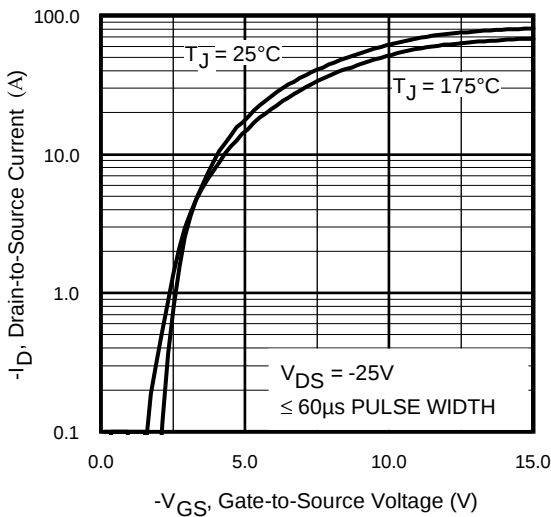




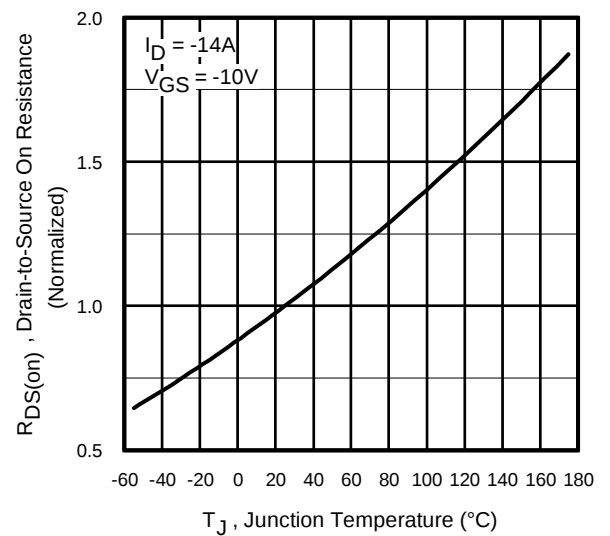
**Fig 1.** Typical Output Characteristics



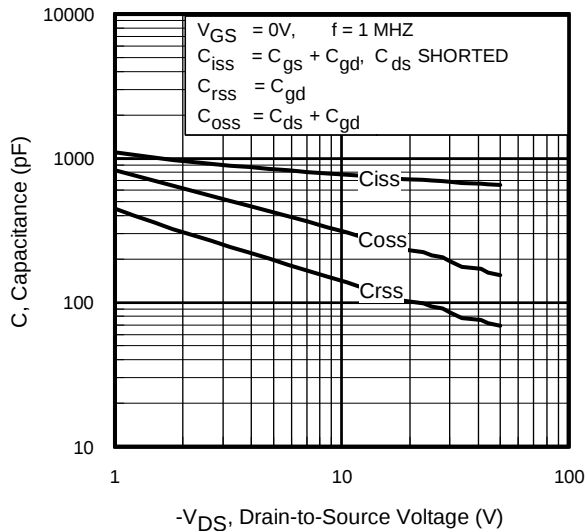
**Fig 2.** Typical Output Characteristics



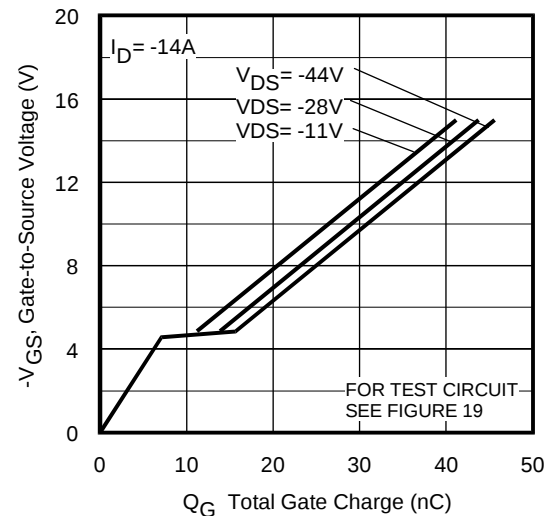
**Fig 3.** Typical Transfer Characteristics



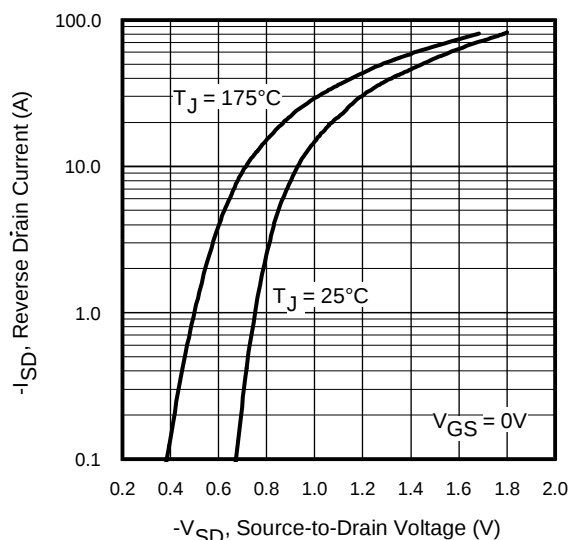
**Fig 4.** Normalized On-Resistance vs. Temperature



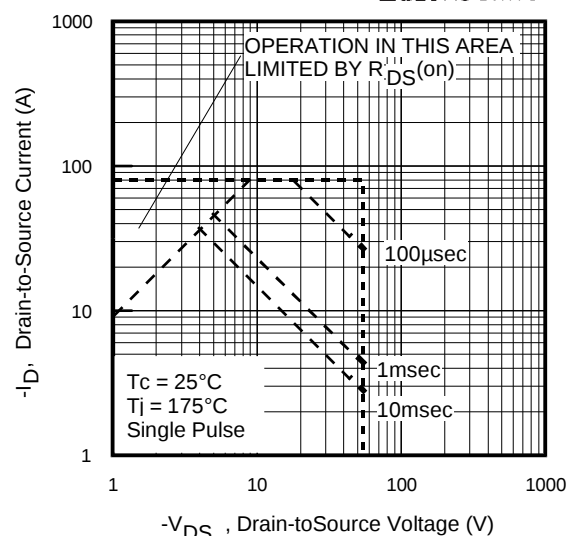
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



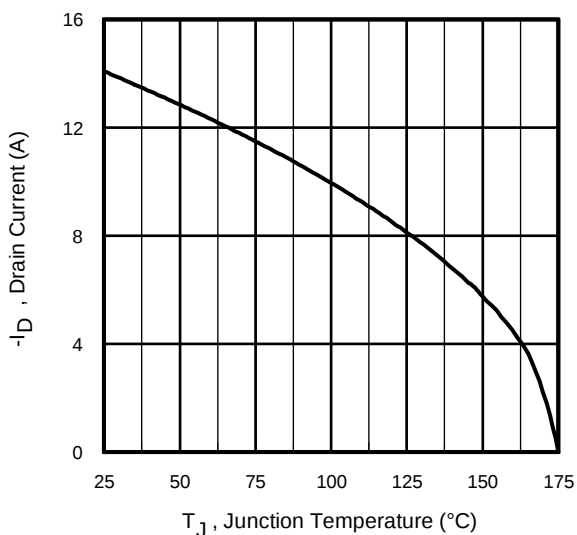
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



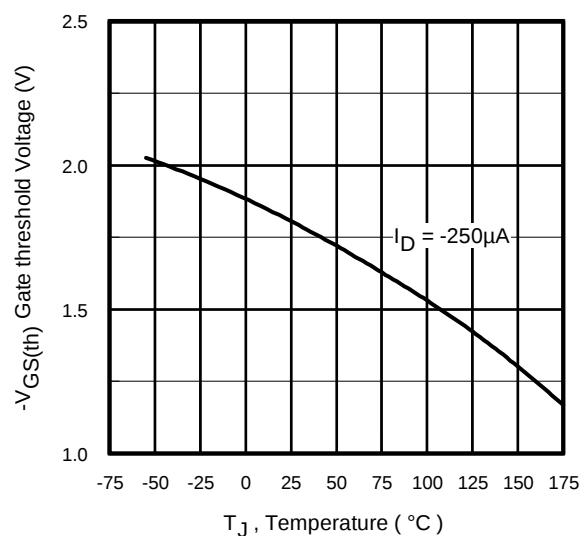
**Fig 7.** Typical Source-Drain Diode Forward Voltage



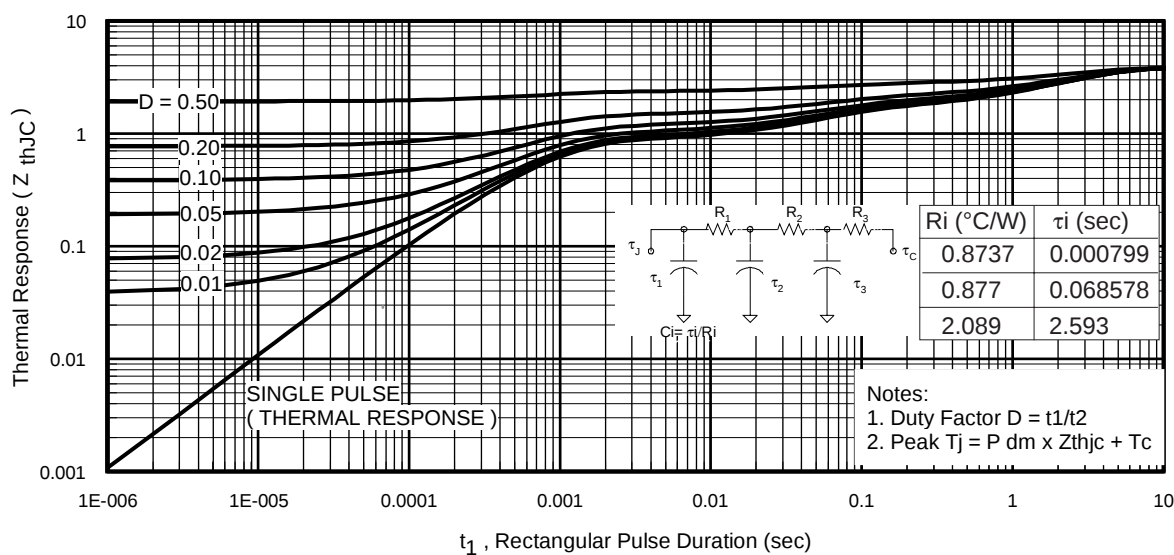
**Fig 8.** Maximum Safe Operating Area



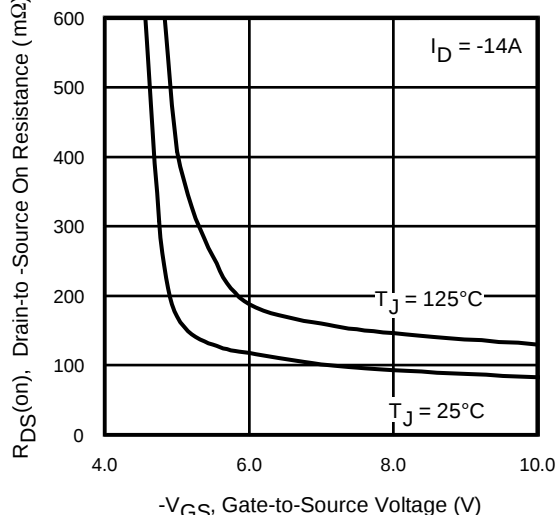
**Fig 9.** Maximum Drain Current vs. Case Temperature



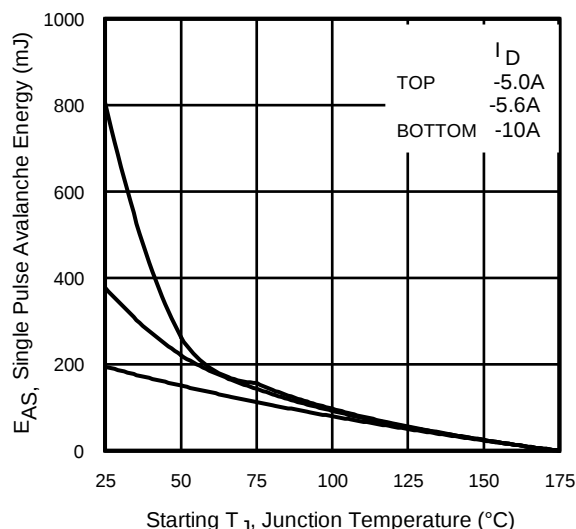
**Fig 10.** Threshold Voltage vs. Temperature



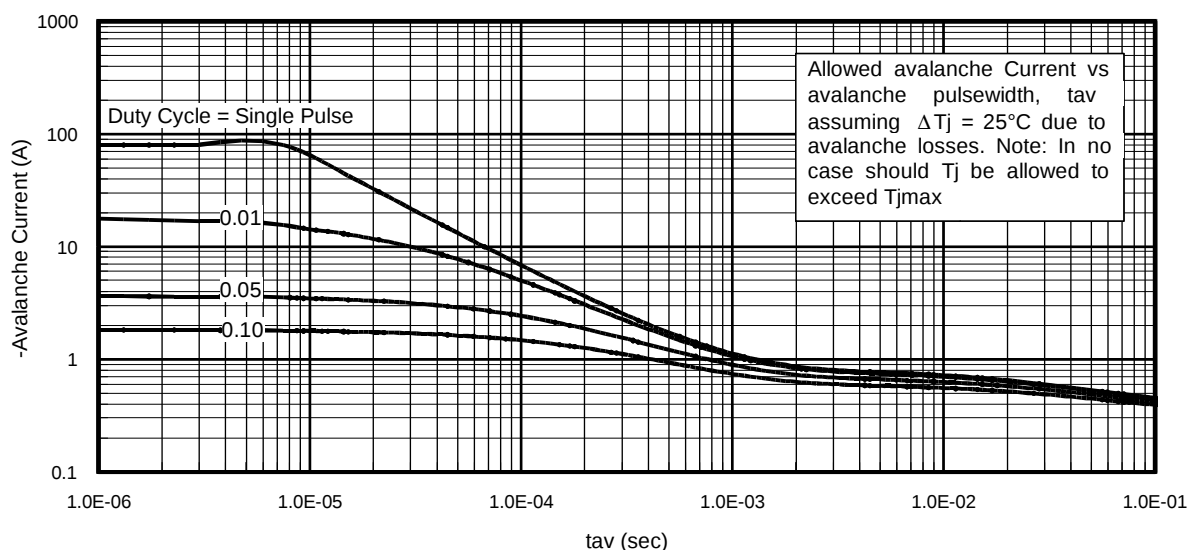
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



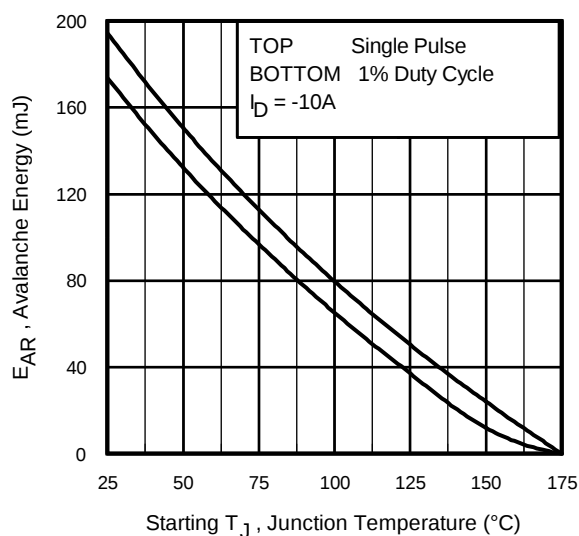
**Fig 12.** On-Resistance Vs. Gate Voltage



**Fig 13.** Maximum Avalanche Energy Vs. Drain Current



**Fig 14.** Typical Avalanche Current Vs. Pulsewidth



**Fig 15.** Maximum Avalanche Energy Vs. Temperature

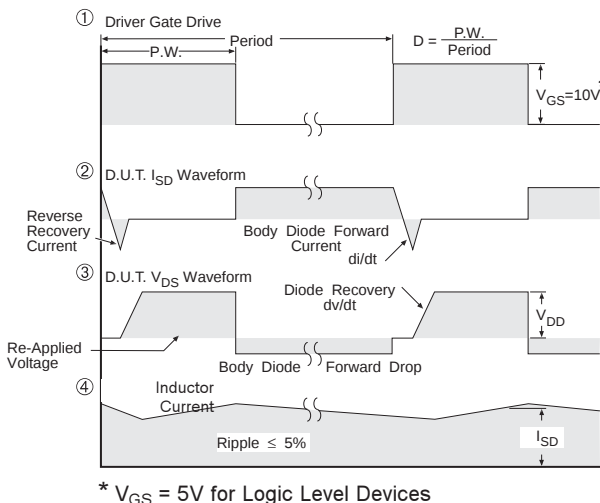
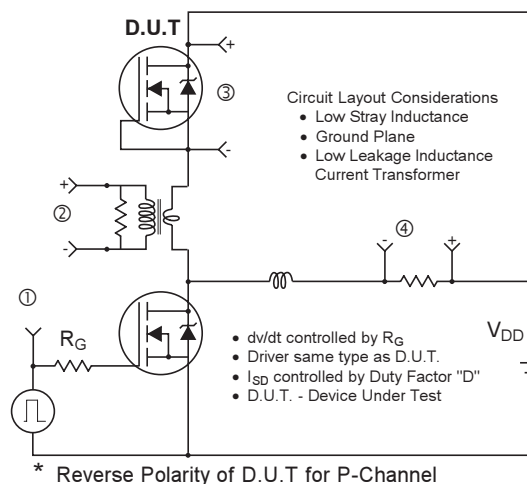
**Notes on Repetitive Avalanche Curves , Figures 14, 15:**  
(For further info, see AN-1005 at [www.irf.com](http://www.irf.com))

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{Jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{Jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 17a, 17b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{Jmax}$  (assumed as 25°C in Figure 14, 15).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see figure 11)

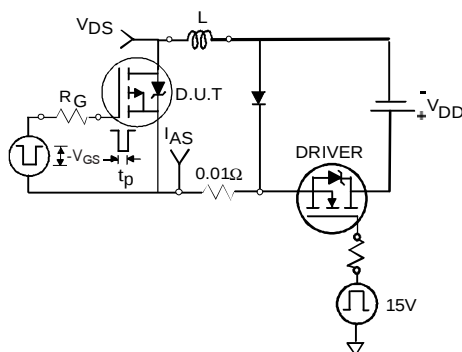
$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

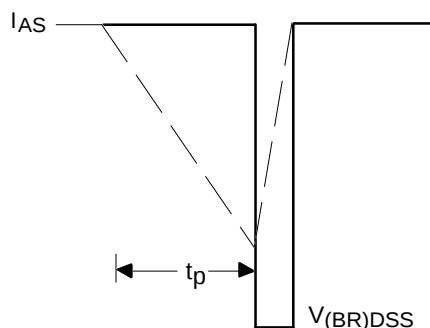
$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$



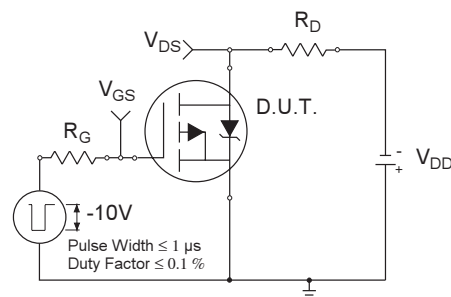
**Fig 16. Peak Diode Recovery  $dv/dt$  Test Circuit for P-Channel HEXFET® Power MOSFETs**



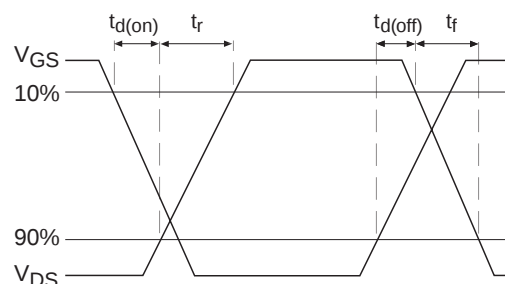
**Fig 17a. Unclamped Inductive Test Circuit**



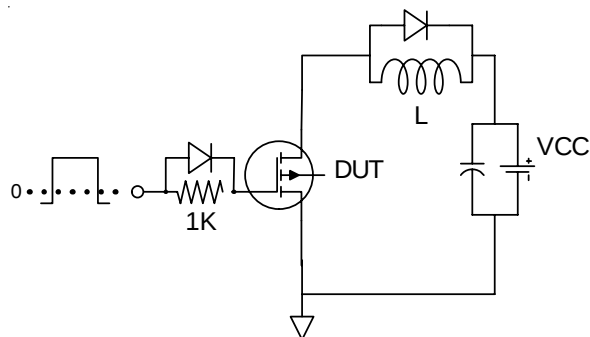
**Fig 17b. Unclamped Inductive Waveforms**



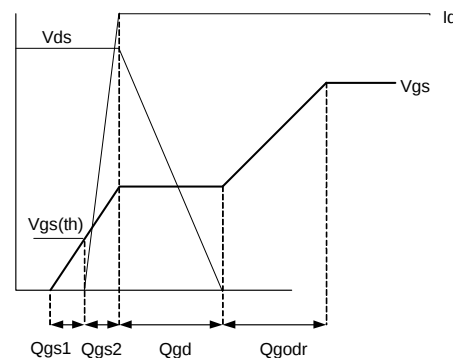
**Fig 18a. Switching Time Test Circuit**



**Fig 18b. Switching Time Waveforms**



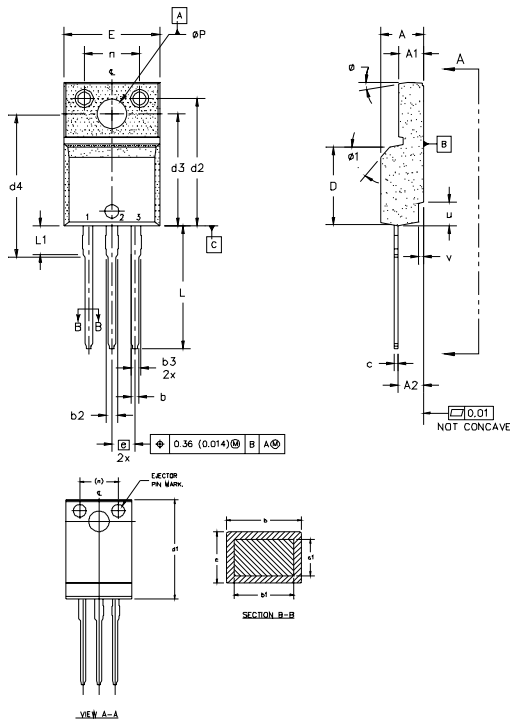
**Fig 19a. Gate Charge Test Circuit**



**Fig 19b. Gate Charge Waveform**

## TO-220 Full-Pak Package Outline

Dimensions are shown in millimeters (inches)



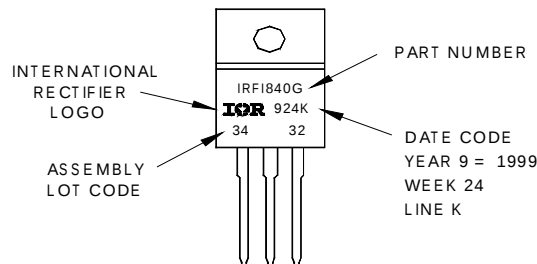
- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M-1994.
  - 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
  - 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
  - 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 5.0 DIMENSION b1 APPLY TO BASE METAL ONLY.
  - 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
  - 7.0 CONTROLLING DIMENSION: INCHES.

| SYMBOL | DIMENSIONS  |       |           |       | NOTES | LEAD ASSIGNMENTS     |
|--------|-------------|-------|-----------|-------|-------|----------------------|
|        | MILLIMETERS |       | INCHES    |       |       |                      |
|        | MIN.        | MAX.  | MIN.      | MAX.  |       |                      |
| A      | 4.57        | 4.83  | 0.180     | 0.190 |       |                      |
| A1     | 2.57        | 2.85  | 0.101     | 0.114 |       | <u>HEXFET</u>        |
| A2     | 2.51        | 2.85  | 0.099     | 0.112 |       |                      |
| b      | 0.622       | 0.89  | 0.024     | 0.035 |       | 1 - GATE             |
| b1     | 0.622       | 0.838 | 0.024     | 0.033 | 5     | 2 - DRAIN            |
| b2     | 1.229       | 1.400 | 0.048     | 0.055 |       | 3 - SOURCE           |
| b3     | 1.229       | 1.400 | 0.048     | 0.055 |       |                      |
| c      | 0.440       | 0.629 | 0.017     | 0.025 |       | <u>IGBTs, CoPACK</u> |
| c1     | 0.440       | 0.684 | 0.017     | 0.023 |       |                      |
| D      | 8.65        | 9.80  | 0.341     | 0.386 | 4     | 1 - GATE             |
| d1     | 15.80       | 16.12 | 0.622     | 0.635 |       | 2 - COLLECTOR        |
| d2     | 13.57       | 14.22 | 0.550     | 0.560 |       | 3 - EMITTER          |
| d3     | 12.30       | 12.92 | 0.484     | 0.509 |       |                      |
| d4     | 8.64        | 9.91  | 0.340     | 0.390 |       |                      |
| E      | 10.36       | 10.63 | 0.408     | 0.419 | 4     |                      |
| e      | 2.54 BSC    |       | 0.100 BSC |       |       |                      |
| L      | 13.20       | 13.73 | 0.520     | 0.541 |       |                      |
| L1     | 3.10        | 3.50  | 0.122     | 0.138 | 3     |                      |
| n      | 6.05        | 6.15  | 0.238     | 0.242 |       |                      |
| p      | 3.05        | 3.45  | 0.120     | 0.136 |       |                      |
| u      | 2.40        | 2.50  | 0.094     | 0.098 |       |                      |
| v      | 0.40        | 0.50  | 0.016     | 0.020 | 6     |                      |
| w      | 3"          | 7"    | 3"        | 7"    |       |                      |
| x      | 45"         |       | 45"       |       |       |                      |

## TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G  
WITH ASSEMBLY  
LOT CODE 3432  
ASSEMBLED ON WW 24 1999  
IN THE ASSEMBLY LINE "K"

**Note:** "P" in assembly line position indicates "Lead-Free"



**TO-220 FullPak packages are not recommended for Surface Mount Application.**

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 3.89\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = -10\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④  $R_\theta$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .
- ⑤ Limited by  $T_{jmax}$ . See Figs. 14, 15, 17a, 17b for repetitive avalanche information

Data and specifications subject to change without notice.  
This product has been designed for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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